NSN 5961-01-237-7347

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-237-7347 **Inclosure Material:** Metal **Overall Length:** 1.253 inches **Mounting Facility Quantity:** Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-4 **Mounting Method:** Threaded stud **Overall Width Across Flats:** 0.437 inches **Thread Size:** 0.190 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 54.0 nonrepetitive peak reverse voltage and 45.0 repetitive peak reverse voltage and 45.0 working peak reverse voltage **Current Rating Per Characteristic:** 600.00 amperes forward current, average preset and 25.00 amperes source cutoff current absolute and 22.50 amperes forward current, average absolute **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Test Data Document:** 81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Thread Series Designator:** Unf **Terminal Type And Quantity:** 1 tab, solder lug and 1 threaded stud **Specification Data:** 81349-mil-prf-19500/553 government specification Shelf Life: N/a **Unit Of Measure: Demilitarization:** No

Mil-std (military Standard): Mil-prf-19500 spec.

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